

Abstracts

The STACKFET: An Improved Implementation of the Dual Gate FET

W.W. Hoppin, S.C. Cripps and J.R. Anderson. "The STACKFET: An Improved Implementation of the Dual Gate FET." 1988 MTT-S International Microwave Symposium Digest 88.2 (1988 Vol. II [MWSYM]): 915-918.

A new method of directly coupling two GaAs FET devices in series has been developed. This structure, the STACKFET, exhibits significantly improved gain performance over previous configurations and was used to design a balanced amplifier module giving 22.5 dB of gain over the 2-8 GHz band.

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